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14. ABSTRACT <p>In this presentation, the major issues, which confronted the formation of very thin layers of silicon (30-100 nm) on sapphire substrates for application to sub 100-nm device technology, will be reviewed. The focus of the investigation was, and still is, to achieve a structure in which the modern CMOS technology, the mainstay technology and workhorse of the electronic revolution, can be affordably implemented. In this context, one approach to the obtention of crystalline, device-quality thin film silicon-on-sapphire (TFSOS), namely the double Solid Phase Epitaxy (DSPE), has achieved truly outstanding results which are presently incorporated into high-performance products, such as phase-locked loop (PLL) ICs for wireless communication, and analog-to-digital converters for space application.</p> <p>Presented at the Lateral Epitaxial Overgrowth Workshop, Juneau, Alaska, August 2-6, 1999.</p>					
15. SUBJECT TERMS thin film silicon-on-sapphire (TFSOS) chemical vapor deposition (CVD)					
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## Silicon-on-Sapphire

### Abstract

The early sixties were at the beginning of the electronics revolution where silicon integrated circuits built their current dominance, fundamentally and pervasively on tailor-made materials, starting at the atomic level. Thin-film deposition techniques, particularly chemical vapor deposition (CVD) and molecular-beam epitaxy (MBE) were developed to provide control over material constituents "in atomic amounts", in order to form the active part of high-performance devices. Nonetheless, the CVD techniques failed to provide a crystalline silicon structure amenable to advanced devices on insulating substrates, particularly sapphire.

In this presentation, the major issues, which confronted the formation of very thin layers of silicon (30-100 nm) on sapphire substrates for application to sub 100-nm device technology, will be reviewed. The focus of the investigation was, and still is, to achieve a structure in which the modern CMOS technology, the mainstay technology and workhorse of the electronic revolution, can be affordably implemented. In this context, one approach to the obtention of crystalline, device-quality thin film silicon-on-sapphire (TFSOS), namely the double Solid Phase Epitaxy (DSPE), has achieved truly outstanding results which are presently incorporated into high-performance products, such as phase-locked loop (PLL) ICs for wireless communication, and analog-to-digital converters for space application.

Besides the materials properties, devices' performances ( $f_t > 100\text{GHz}$ ) and circuits' applications (analog and mixed signals), present investigations aimed at producing stressed layers of  $\text{Si}_{1-x}\text{Ge}_x$  ( $x > 0.75$ ) grown on TFSOS will also be described. Based on the present results, TFSOS could become entrenched, as CMOS, as new materials and devices appear – witness the recent success in developing highly-engineered structures with SiGe on TFSOS (hole mobility, through Hall measurements, is in excess of  $800\text{cm}^2/\text{V}\cdot\text{sec}$ ) – using the established industrial infrastructure.

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# COMMUNICATION and INFORMATION SYSTEMS DEPARTMENT

## *Lateral Epitaxial Overgrowth Workshop Silicon-on-Sapphire Technology*

Juneau, Alaska--August 2-6, 1999

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# **TFSOS**

- **Introduction — A historical perspective**
- **The Vision: Thin Film Silicon on Sapphire**
- **Comparison with other SOI alternatives**
- **Recent results for SiGe –The march of Technology**
- **Prognosis-Trend**
- **Conclusion**

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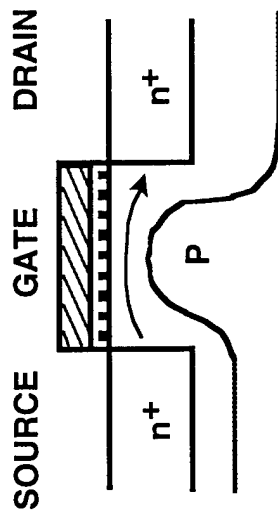
## **Collaborators**

- **Space and Naval Warfare Systems Center, San Diego**
- **University of California at San Diego (UCSD)**
- **International Business Machines (IBM)**
- **Auburn University**
- **Oklahoma State University**
- **Saphikon**
- **Lawrence Semiconductor**
- **Massachusetts Institute of Technology (MIT)**
- **Lincoln Laboratory**
- **University of Florida, Gainesville**
- **Peregrine Semiconductor Corporation**
- **Northrup Grumman**
- **Rockwell International (Science Center)**

# Conventional Microelectronics

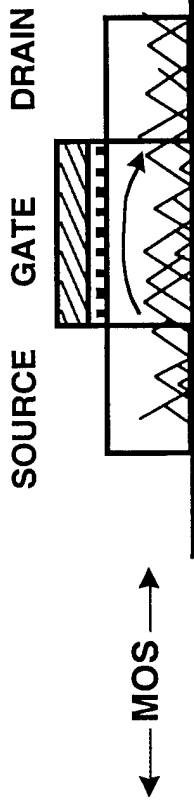
## A Historical Perspective

Bulk Silicon

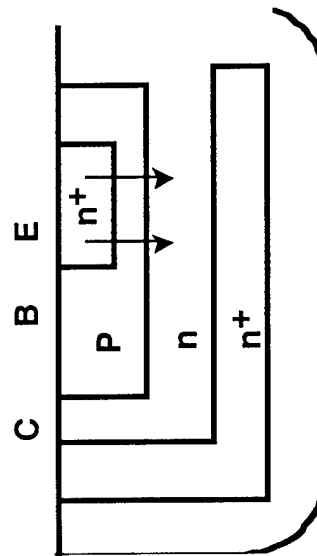


Parasitic Capacitor

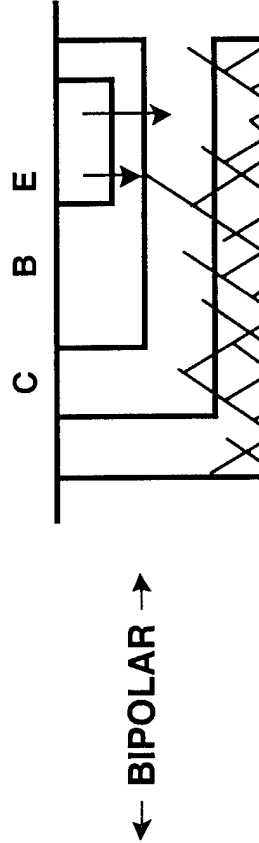
Silicon on Sapphire (SOS)



Sapphire



Parasitic Capacitor



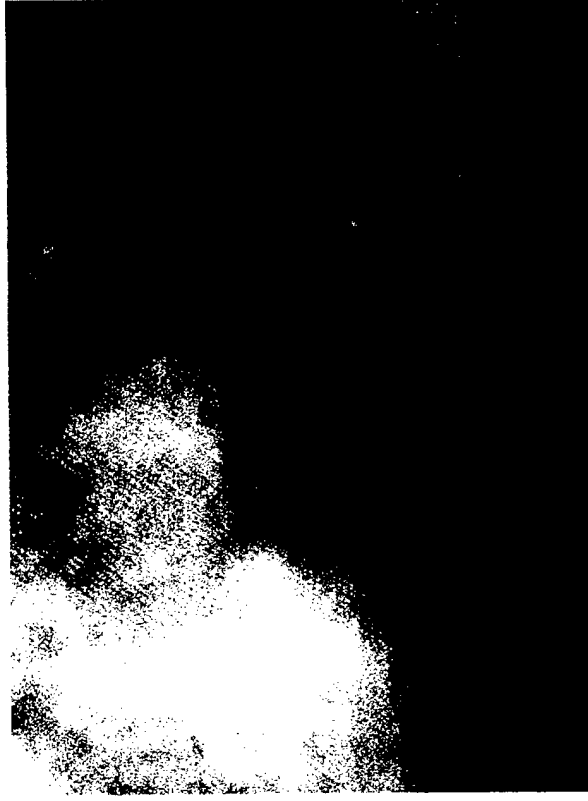
Sapphire

H.M. Manasevit & W.S. Simpton. JAP, 35, pg 1349, 1964.

## Thin Film Silicon on Sapphire TEM Images: Before & After Improvement Process



Before Improvement

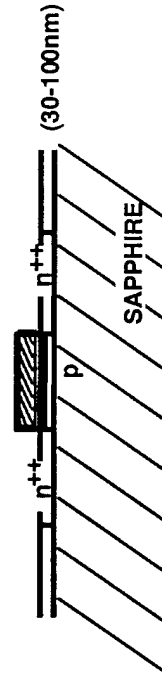
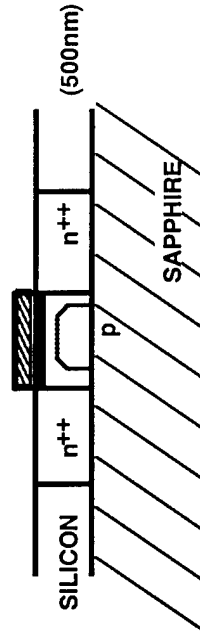
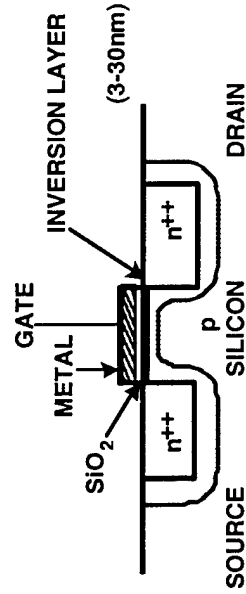


After Improvement

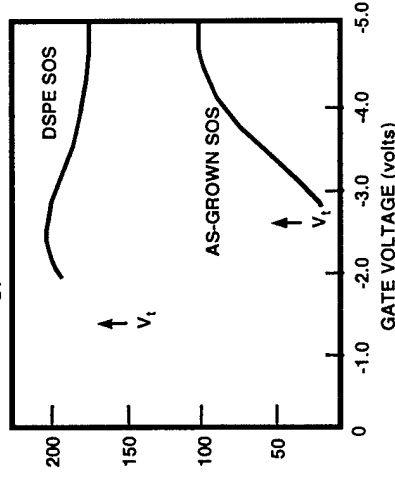
# Thin Film Silicon on Sapphire

## The Vision

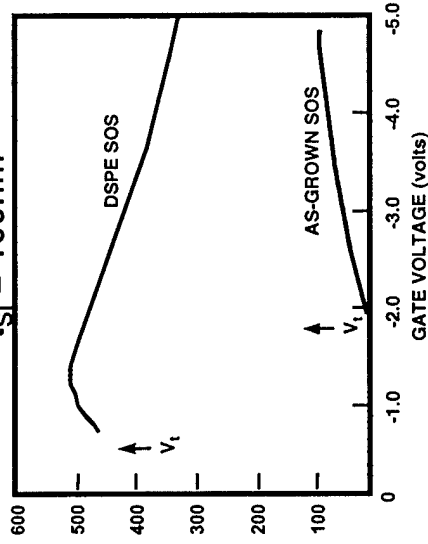
### Scaling Limits



### Low-Field Hole Mobility $t_{\text{Si}} = 100\text{nm}$



### Low-Field Electron Mobility $t_{\text{Si}} = 100\text{nm}$



G.A. Garcia, R.E. Reedy.  
*Elect. Lett.*, **22**(10), p. 537-538, 8 May 1986.

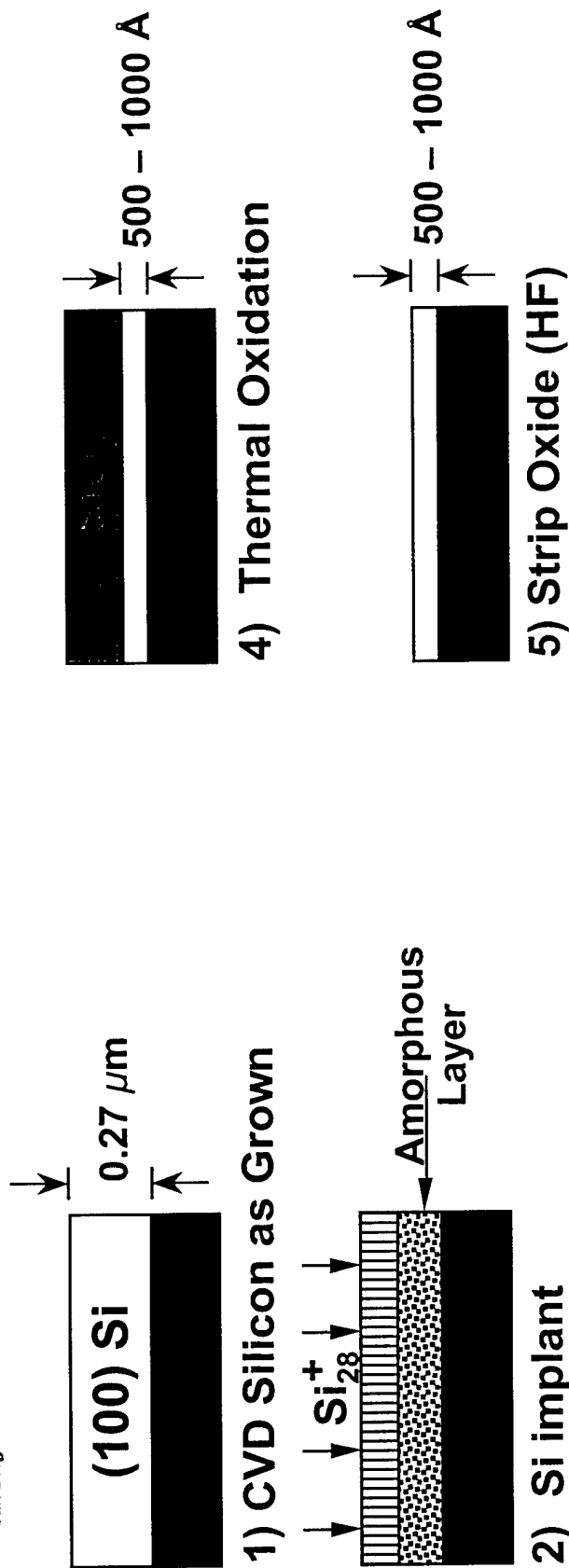
G.A. Garcia, R.E. Reedy,  
M.L. Burgener. *EDL*, **9**(1),  
p. 32-34, Jan. 1988

M. Roser, *et al.*. 50th Device  
Research Conference,  
June 22-24, 1992



# ULTRATHIN SOS

## Improvement and Thinning Sequence

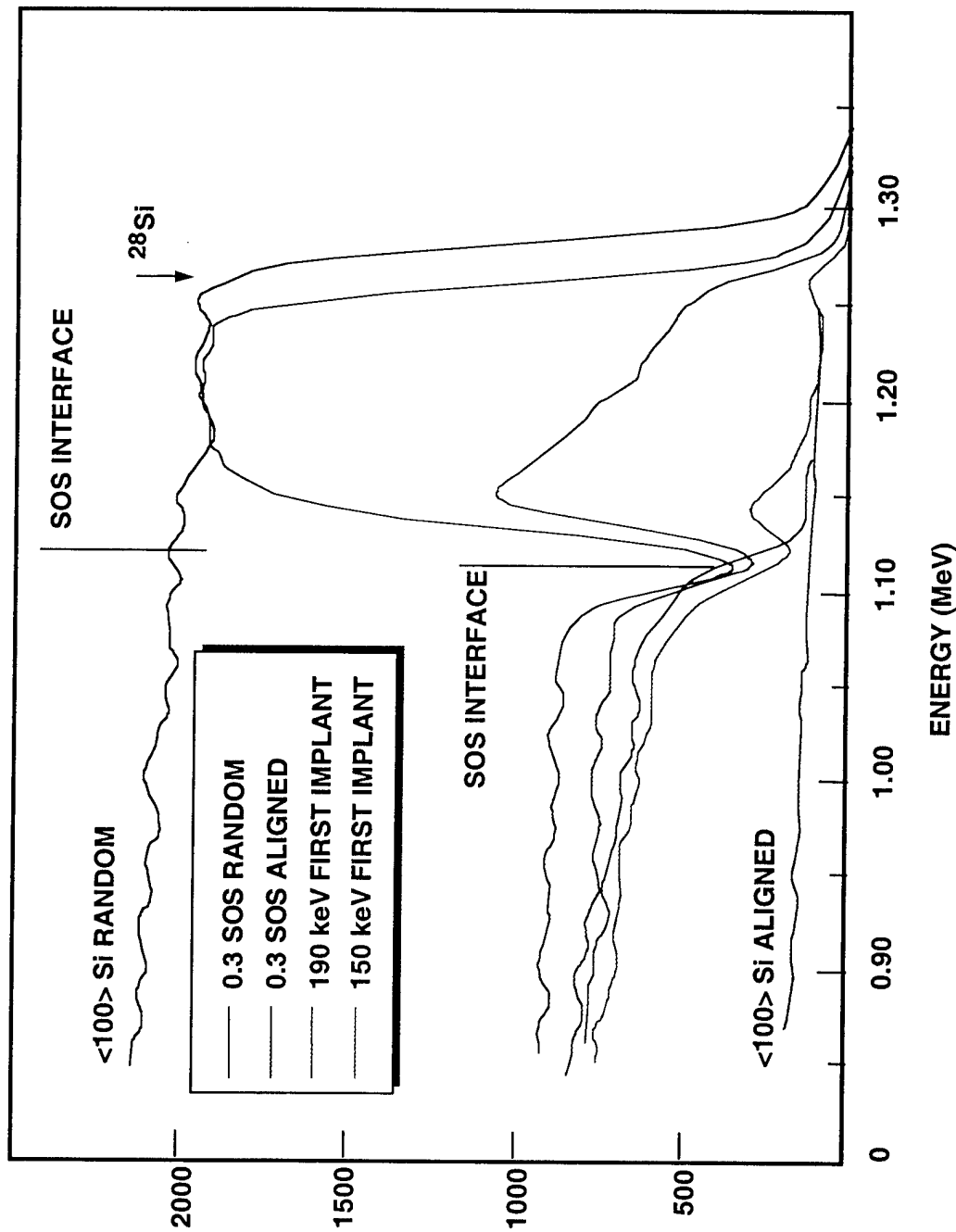


**Final Product:**  
Device Quality Single  
Crystal Silicon Film Under  
Compressive Strain

S.S. Lau *et al.*, *APL*, **34**(1), p. 76-78, 1 Jan. 1979.

T. Yoshii *et al.*, *JJAP*, Part 1, **21**(suppl.21-1), p.175-179, 1982.

# RBS Data, TFSOS

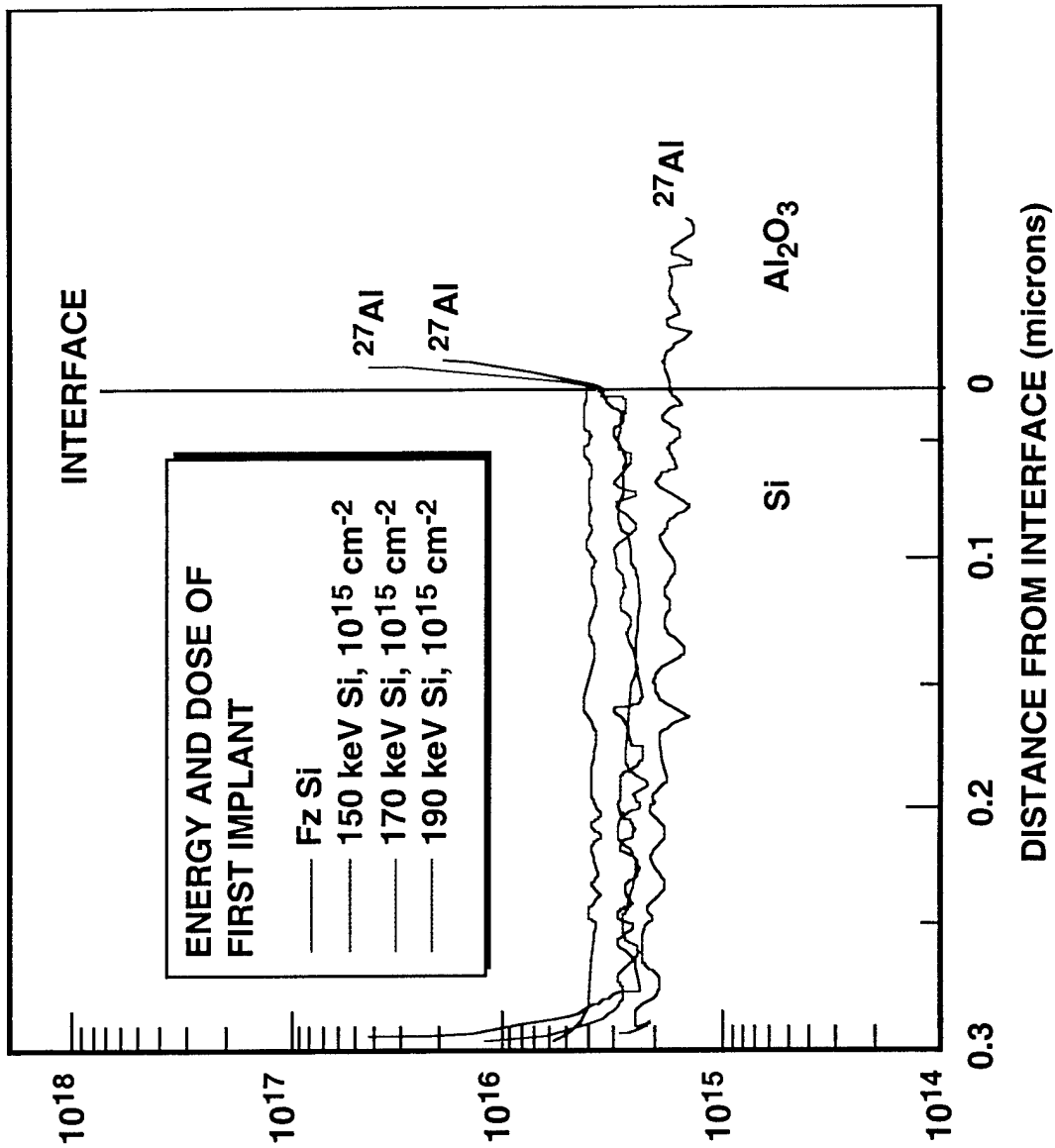


G.A. Garcia, R.E. Reedy. *Electronics Let.*, **22**(10), p. 537-538, 8 May 1986.  
R.E. Reedy, G.A. Garcia. MRS Symposium Proc. **107**, p. 365-376, 1988.



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# Auger Analysis, TFSOS



R.E. Reedy, T.W. Sigmon, L.A. Christel, *APL*, 42(8), p. 707-709, 15 April 1983.



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# Thin Film CMOS/SOS vs. Other Silicon Implementations

## Relative to Bulk CMOS

- Reduced parasitic capacitances
  - less junction capacitances and higher speed)
- Reduced short channel effects
- Better device isolation
  - Latchup suppression
  - Lower body effect
  - Wider operating temperature
- Simple mesa fabrication
- Radiation hardness

## Relative to SIMOX/BESOI

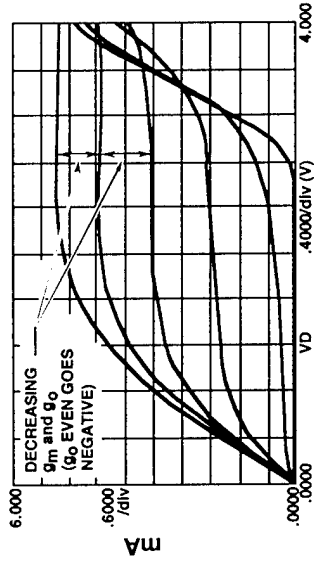
- Lower loss dielectric substrate
  - Lower substrate capacitance
  - Higher Q passive elements
- Lower minority carrier lifetime
  - Parasitic bipolar suppressed
  - Higher S-D breakdown voltage
- Higher thermal conductivity than  $\text{SiO}_2$ 
  - Reduced self-heating effects
- Enhanced hole transport properties
  - PMOS closer to NMOS in size,  $f_T$ ,  $f_{\text{Max}}$
  - Enhanced CMOS performance
- 6-in wafers available, 8-in also available
- Lower cost/Process Simplicity
- Much reduced Floating Body Effect
  - Low leakage  $I_{\text{off}}$  (digital)
  - No Kink Effect in I-V (analog)
- No Transient Hysteresis (low frequencies)



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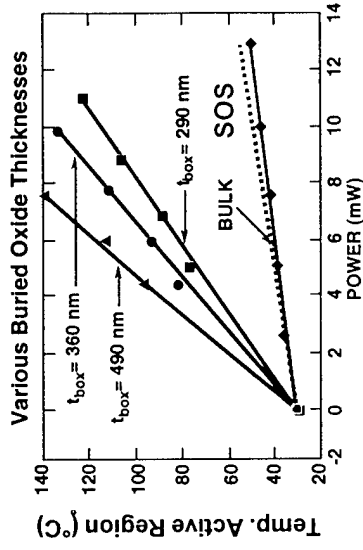
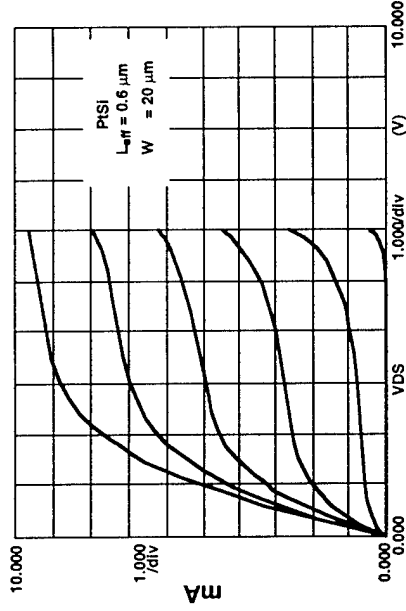
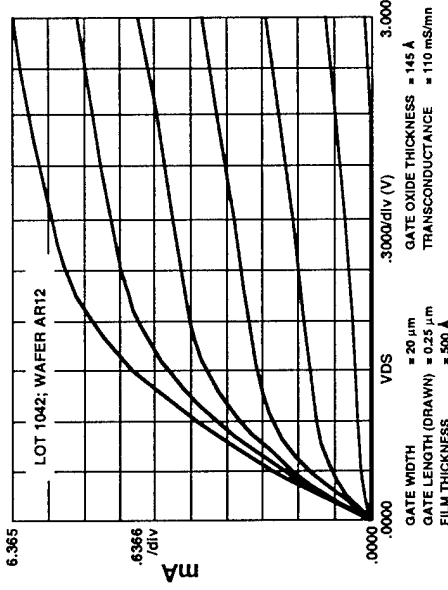
# Thermal Effects Thin Film Silicon on Sapphire vs. SIMOX

SIMOX



$W_{eff} = 10 \mu m$   
 $L_{eff} = 0.3 \mu m$   
 $T_{st} = 70 nm$   
 $T_{ox} = 10 nm$   
 $T_{box} = 360 nm$   
 $N_{sub} = 3 \times 10^{17} cm^{-3}$

TFSOS



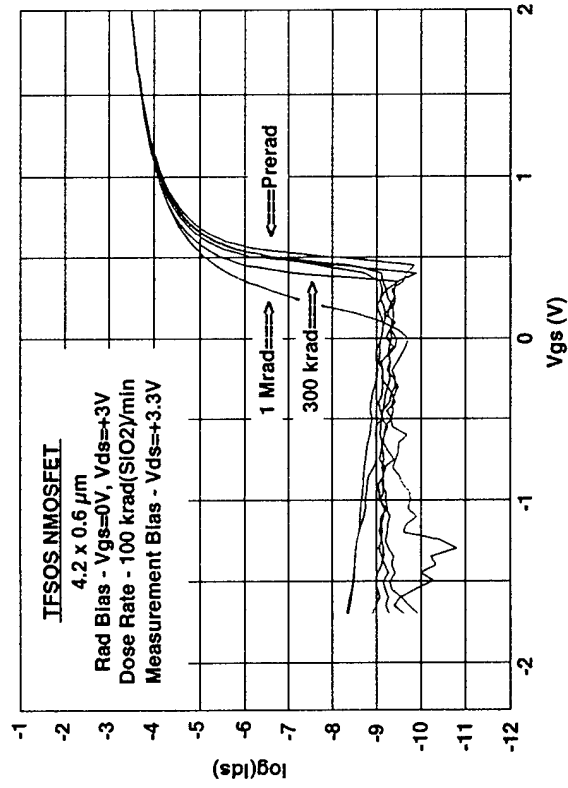
SOS Data:  
 M. Wetzel, UCSD Ph.D.  
 Thesis (to be published)

MIT data;  
 Courtesy Prof. D. Antoniadis

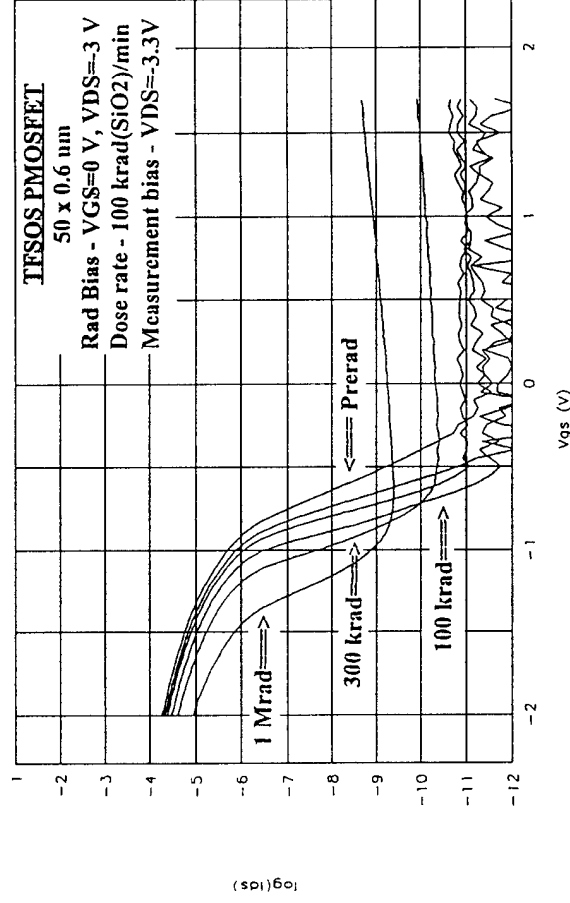


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# Radiation data for TFSOS MOSFETs



n-MOSFET



p-MOSFET

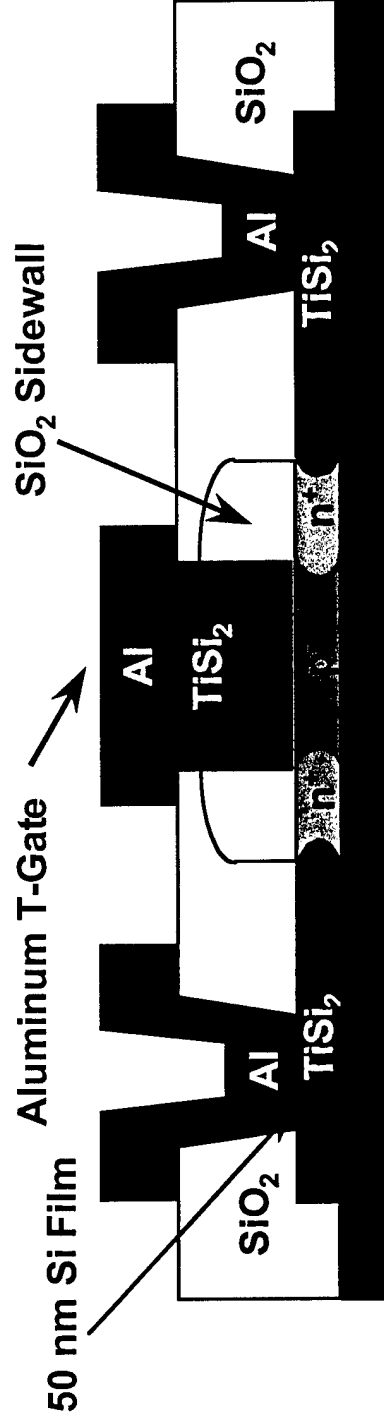
## Thin Film Silicon on Sapphire

- T-Gate used to decrease  $R_g$
- Record high  $f_t, f_{\max}$  microwave transistor
- Record low noise microwave transistor

$$f_{\max} = \frac{f_t}{2\sqrt{2\pi f_t R_g C_{gd} + G_o [R_g + R_s]}}$$

$$F_{\min} = 1 + kL f \sqrt{g_m [R_s + R_g]}$$

Device	$L_{g,drawn} (\mu m)$	$f_t$ (GHz)	$f_{\max}$ (GHz)	w/o T-Gate	@ 2GHz	
NMOS	0.5	25	66/11	$f_{\max}$ (GHz)	$F_{\min}$ (dB)	$G_a$ (dB)
PMOS	0.5	14	41/7		0.9	21
					0.9	13





# NOISE COMPARISON

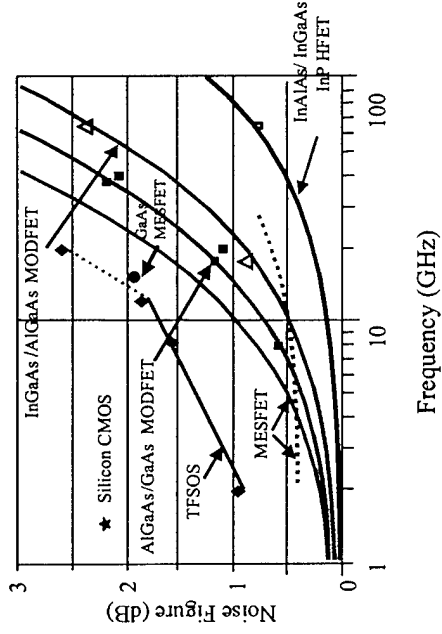
	2 GHz F <sub>min</sub> G <sub>a</sub>	8 GHz F <sub>min</sub> G <sub>a</sub>	12 GHz F <sub>min</sub> G <sub>a</sub>	L <sub>g</sub> ( $\mu$ m)	Technology
TFSOS:					
NMOS [9]	0.9    21	1.4    11	1.8    8.5	0.5	TF SOS
PMOS [9]	0.9    13	1.3    4.7	-    -	0.5	TF SOS
Other Si:					
NMOS [1]	1.5    18	3.25    8.5	-    -	0.25	MICROX
PMOS [1]	2.7    15	-    -	-    -	0.25	MICROX
NMOS [2]	0.8    17	1.6    9.8	2.2    6.8	0.6	MICROX
NMOS [3]	5.0    6.4	-    -	-    -	1.0	BESOI
Other:					
HBT [4]	0.5    12	0.8    -	1.0    -	2 x .6 x 8	SiGe
HBT [5]	0.46    11.6	1.4    -	2.0    -	3.5 x 3.5	InP/InGaAs
PHEMT [6]	0.2    -	.33    -	0.41    13	0.15	GaP/InGaAs
JFET [7]	0.4    -	1.6    -	-    -	0.5	GaAs
MESFET [8]	0.4    23	0.5    15	0.5    13	0.11	GaAs

1. EDL, May 1993, pg. 219, Hanes *et al.*
2. MTT-S Workshop, May 1995, Agarwal *et al.*
3. EDL, Jan 1991, pg. 26, Caviglia, *et al.*
4. MTTs, 1994 pg 1167, H. Schumacher, *et al.*
5. EDL, Oct 1989, Y.K. Chen *et al.*
6. EDL, Aug 1983, pg. 406, M. Takikawa *et al.*
7. EDL, Sept. 1993, D. Scherrer *et al.*
8. TED, Feb 1999, pg. 310, Kimo *et al.*
9. TED, May 1998, pg. 1047-54, R. Johnson *et al.*



# Noise Figure Results for Different Technologies: Transistors and LNAs

Noise figures of FET's based on GaAs and of Si CMOS transistors.  
After L.M. Franca-Neto *et al.*, *IEDM*, pg. 305-307, 1997.



Recent Results on Low Noise Amplifier Designs  
After L.M. Franca-Neto *et al.*, *IEDM*, pg. 305-307, 1997.

Technology	F (GHz)	NF (dB)	Author
1 micron GaAs FET	1	2.2	Cioffi, IMMMCS, 1992
1 micron GaAs FET	1.6	2.2	Cioffi, IMMMCS, 1992
0.3 micron GaAs FET	1.9	2.0	Nakatsugawa, GaAs-IC Symp, 1993
1 micron GaAs FET	1.9	1.5	Heaney, GaAs-IC Symp., 1993
0.3 micron GaAs FET	1.6	2.5	Imai, IEEE-Trans. MTT, 1991
0.5 micron CMOS	0.9	2.2	Karanicolas, ISSCC, 1996
1 micron CMOS	0.9	3.5	Rofougaran, IEEE-JSSC, 1996
0.6 micron CMOS	1.5	3.5	Shaeffer, IEEE-JSSC, 1997
0.5 micron CMOS/SOS	2.4	2.2	Johnson, R.A. <i>et al.</i> , IEEE-TED, 1998



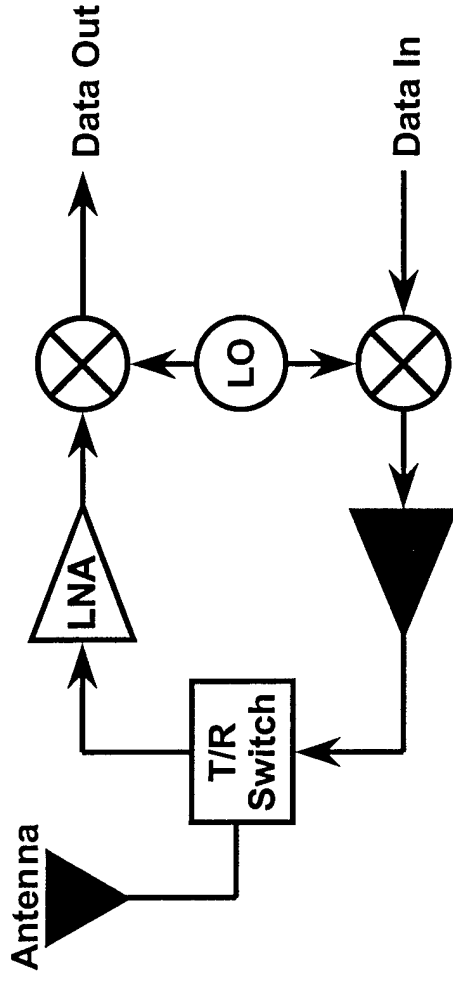
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## Thin Film Silicon on Sapphire Wireless Communications Applications

### • Demonstrate SOS technology application to L and S band Applications

### • Test Vehicle: 2.4 GHz transceiver

- **Transmit / Receive Switch** R.A. Johnson et al., *IEE Elect. Lett.*, 33(15), pg. 1324-1326, 17 July 1997.
- **Mixer** R.Johnson et al., *TED*, 45(5), pg. 1047-1054, May 1998.
- **Low Noise Amplifier** R.A. Johnson et al, *IEEE Microwave & Guided Wave Letters*, 7(10), pg. 350-352, Oct.1997.
- **Power Amplifier** M. Wetzel et al., 1st Annual UCSD Conference on Wireless Communications, March 8-10, 1998



## Why CMOS/SOS at Microwave/RF Frequencies

- Low power, high noise immunity
- Cost
  - High integration level (VLSI) / Mature technology
    - ➔ Competitive manufacturing cost (7-10% higher than CMOS bulk Si)
    - ➔ Complexity => Low cost per functional unit
    - ➔ 6" wafers available with low defect density
  - Reduced processing steps (mesa isolation)
    - ➔ Much lower cost than bipolar, HBTs (Si or III-V's)
  - Inexpensive material (except vs. bulk silicon)
  - Leverage off Si manufacturing base
- Mixed analog / digital integration
  - Low loss dielectric substrate (isolation/ no latch up)
    - ➔ Low substrate capacitance
    - ➔ High Q passive elements
  - $f_{\max} = 66 \text{ GHz}$  ( $L_{\text{eff}} \sim .3 \mu\text{m}$ ), Noise Figure < 1 dB optically defined devices
  - $f_t > 100 \text{ GHz}$  ( $L_{\text{eff}} \sim .1 \mu\text{m}$ ) (x-ray)
  - Very high linearity at low power (good IP3)
  - Excellent ESD protection with low parasitics
- SiGe/SOS,  $m_h > 800 \text{ cm}^2/\text{V}\cdot\text{sec}$  (pMODFET,  $L_g = 0.1 \mu\text{m}$ ,  $g_m = 420 \text{ mS/mm}$ )
  - > much higher speed CMOS with lower power



## Why CMOS/SOS at Microwave/RF Frequencies

- Low power, high noise immunity
- Cost
  - High integration level (VLSI) / Mature technology
    - ➔ Competitive manufacturing cost (7-10% higher than CMOS bulk Si)
    - ➔ Complexity => Low cost per functional unit
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- SiGe/SOS,  $m_h > 800 \text{ cm}^2/\text{V}\cdot\text{sec}$  (pMODFET,  $L_g = 0.1 \mu\text{m}$ , fabricated; to be published)
  - > much higher speed CMOS with lower power



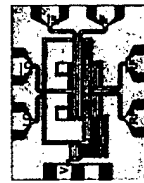
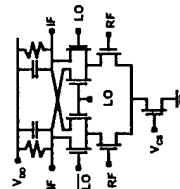
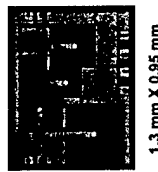
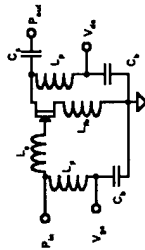
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# Circuit Level SOS rf Results

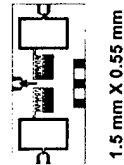
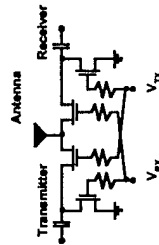
## FY98 Circuits Test Results

LNA, MIXER and T/R Switch Fabricated in TFSOS

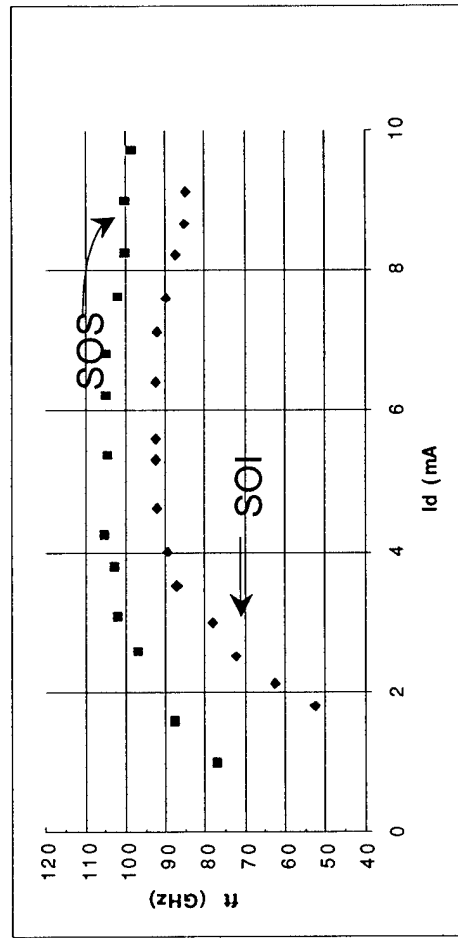
MEASURED				
	Operating Freq	Gain	NF (50 <sup>Ω</sup> )	IP3 (output)
LNA	2.4 GHz	11 dB	2.2 dB	14 dBm
Power@vdd				
				13.2mW@1.5V
Mixer	Center=2.4 GHz	-5 dB		
	IF=250 MHz			5 dBm
				8.4mW@1.5V



MEASURED				
	Operating Freq	Insertion Loss	Isolation	IP3
T/R Switch	1-5 GHz	1.7-2 dB	30 dB	8 dBm
		0.6-0.7 db	20 dB	



- Record high  $f_t$  ( $> 105$  GHz)
- CMOS inverter delay  $< 8$  psec at RT; 6 psec @ 77K, close to JJ speed;
- Record low noise (0.9 dB NF @ 2GHz), resulting in low noise front end  
==> MAKES HIGH SPEED, HIGH RESOLUTION A/D/C possible
- Record BW (10 GHz) for distributed amplifier

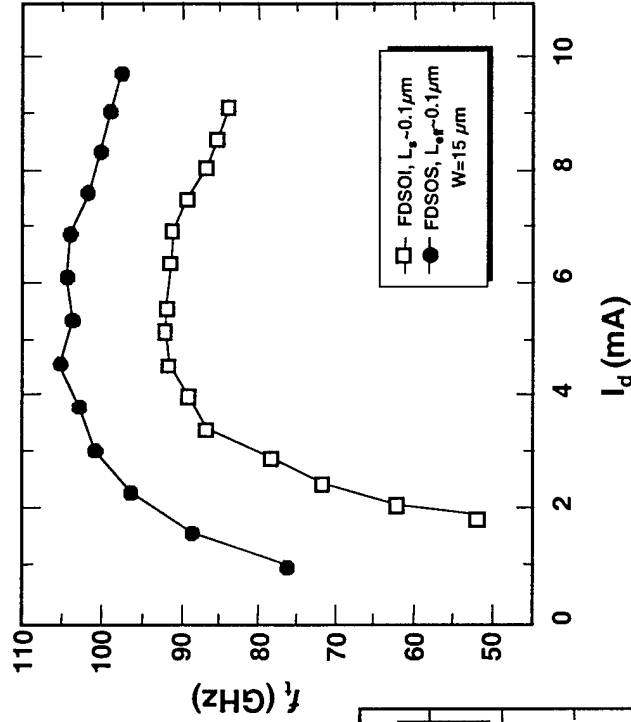


$F_t$  vs.  $I_{ds}$

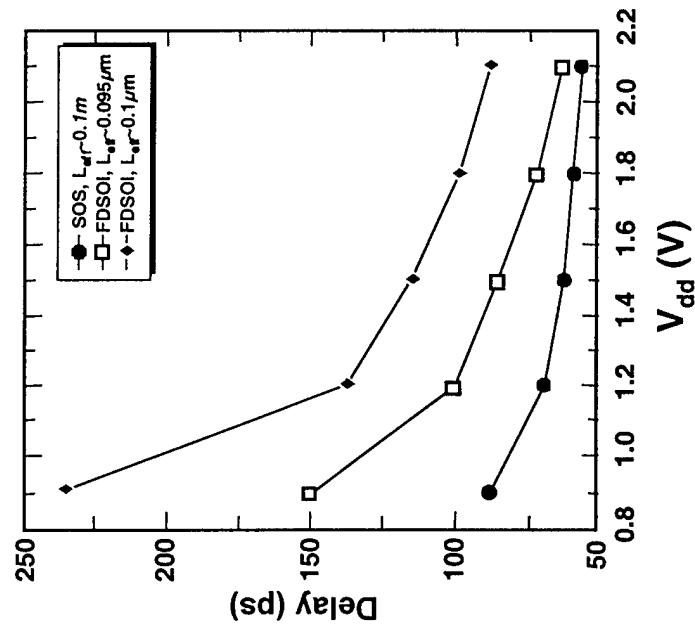
# TFSOS vs. TFSOI RF Data

C. Wann *et al.* ISSCC, Feb. 1998  
C. Wann *et al.* EDL, 18(12), pg. 625-627, Dec. 1997

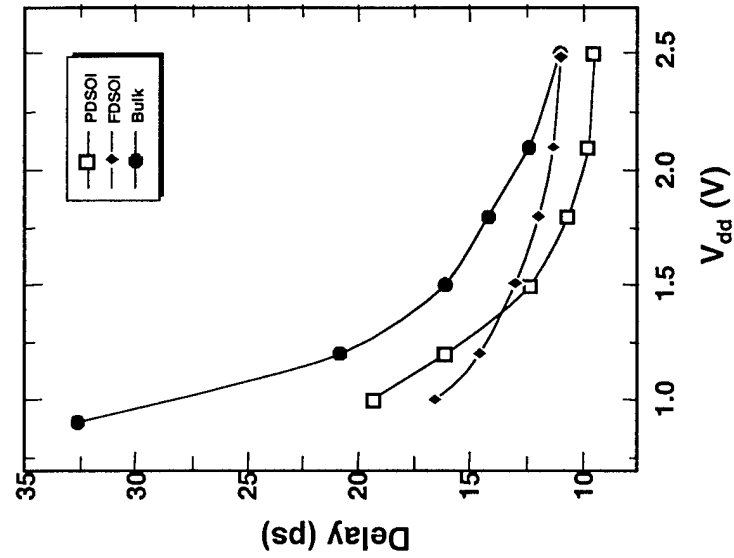
$f_t$  vs.  $I_d$



Unloaded 3-way  
NAND Delay vs.  $V_{dd}$



Delay per Stage vs.  $V_{dd}$



# SPAWAR COMPARATIVE STUDY of CMOS on TFSOS vs.



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## SIMOX vs. BULK SILICON

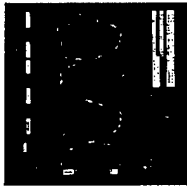


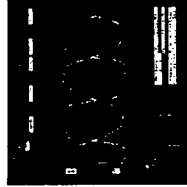
### Accomplishment

#### Objective:

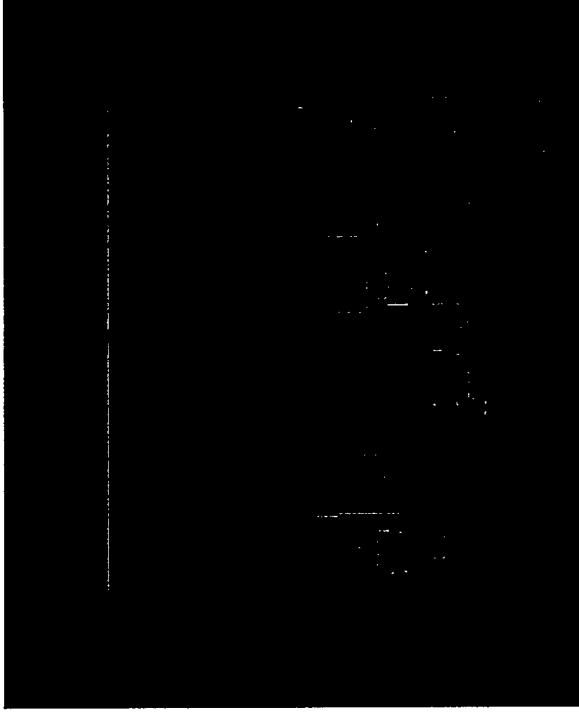
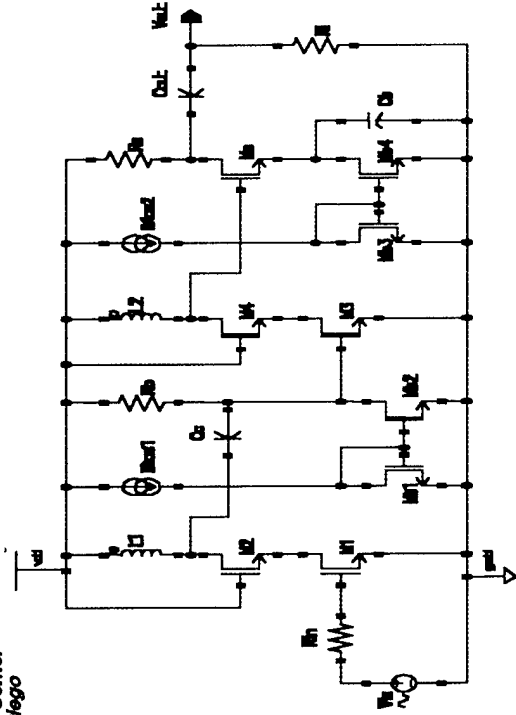
- Determine the comparative CMOS-based alternatives (bulk Si, SIMOX, TFSOS) to implement low power, high frequency, cost-effective VLSIC technology at  $\leq 100\text{nm}$  regime in an environment conducive to manufacturing.

#### Accomplishment:

- Test vehicle: 4-bit, 10 Gps A/D/C.

Comparator Bank	Bubble Detector	Encoder Latch	Output Buffer		
					
$f_{\text{max}} = 10 \text{ GHz}$ goal; $f_{\text{max}} = 7.5\text{-}8 \text{ GHz}$ experimental					
Comparator Bank		Bubble Detector	Encoder	Total Delay	Clock
Delay $= t_d \ln 2^n$ (pS)		Delay (pS)	Delay (pS)	(pS)	$f_{\text{max}}$ (GHz)
CMOS/Si Bulk	108	47	76	231	4.1
CMOS/SIMOX	86	37	60	183	5.5
CMOS/TFSOS	56	29	46	131	7.5-8

## 13-GHz Tuned Amplifier



- Demonstrated Functional Samples (Body-Tied and Floating Body) on Bulk, SOI, and SOS wafers.
- The Peak Gain is ~15dB for SOS Samples.
- Amplifiers with Floating Body have ~5dB Higher Gains.
- Bulk Samples Have Less than 0dB Gain
- SOS Samples Have Significantly Better Characteristics than SOI and Bulk Samples.

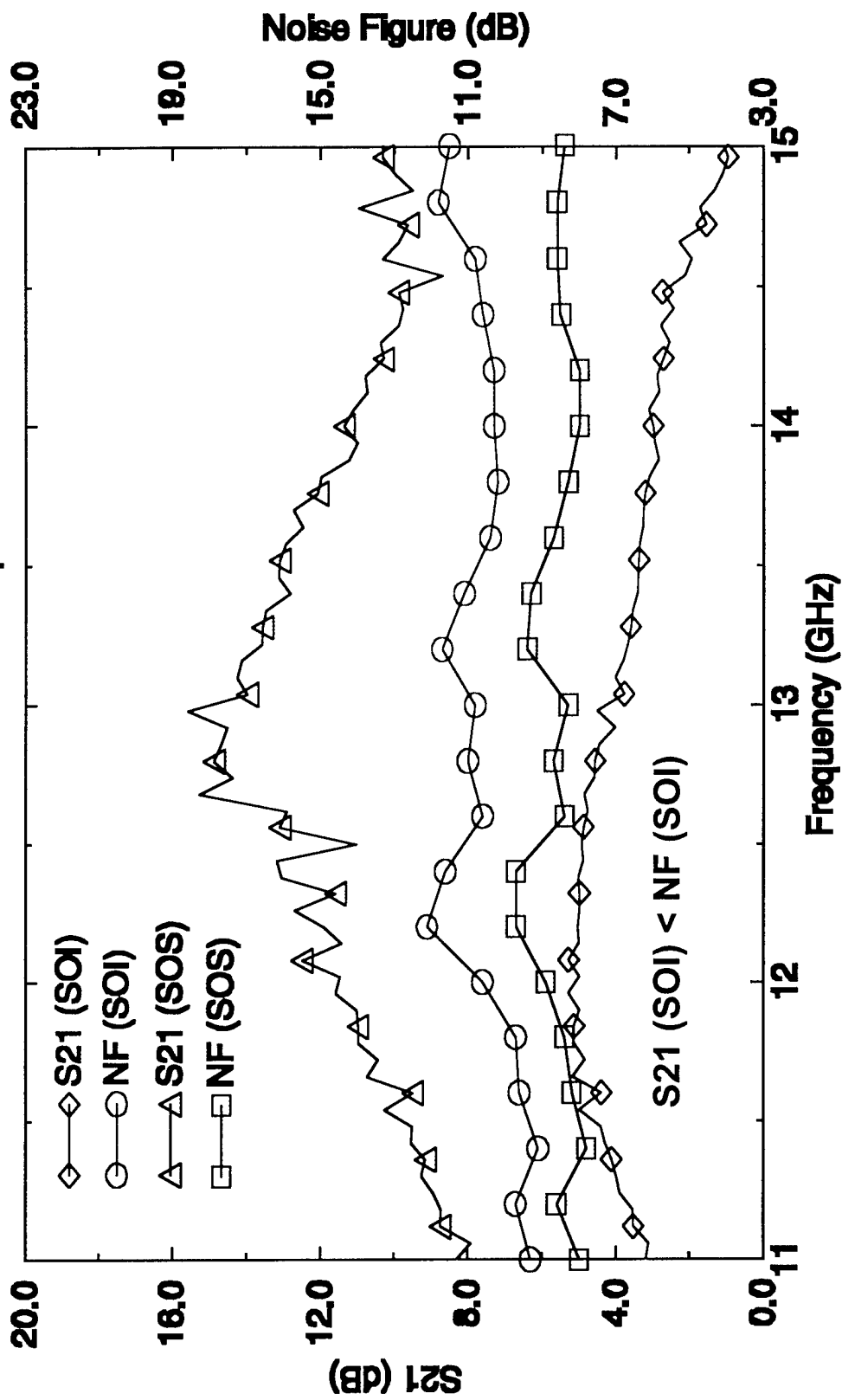
K.K. O *et al.* GOMAC, March 1998.

Yo-Chuol Ho, *et al.* Custom Integrated Circuits Conference, April 1998.

K.-H. Kim *et al.* ISSCC, Feb. 1998.



# Transducer Power Gain & Noise Figure PD Floating-Body SOS and SOI 13-GHz Tuned Amplifier



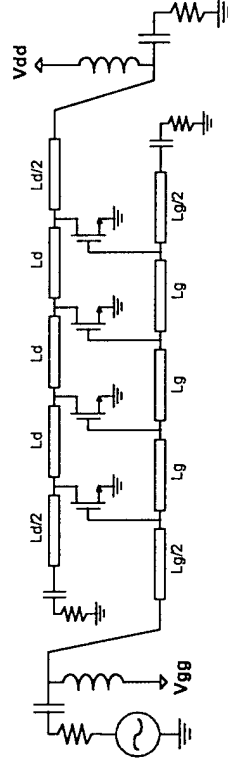
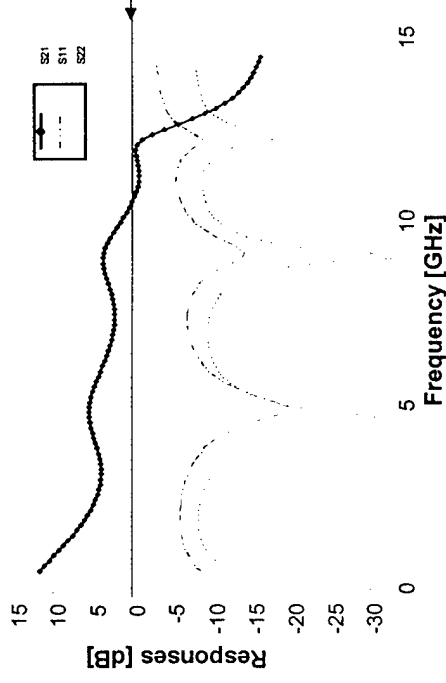


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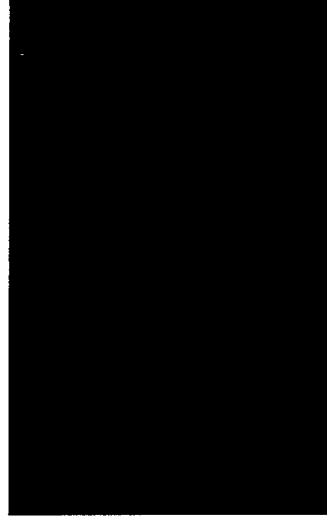
# Distributed Amplifier

Broadest bandwidth ever  
reported for any Si-FET  
distributed amplifier  
300 um gate width, 4 stages

SOS Distributed Amplifier  
300 $\mu$ m x 4 stages (External Matching)

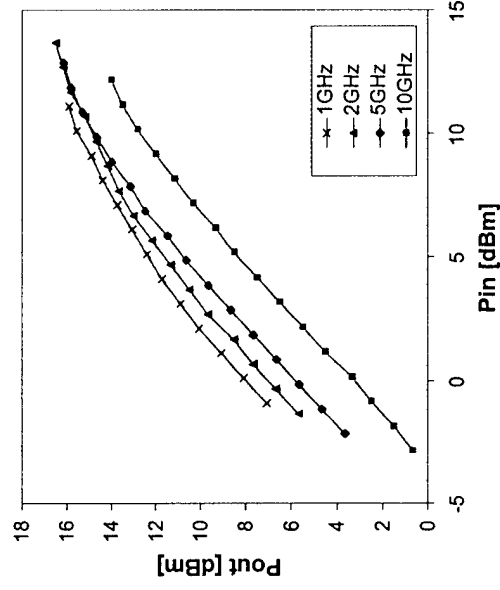


Schematic



Photograph of Amplifier

Frequency response

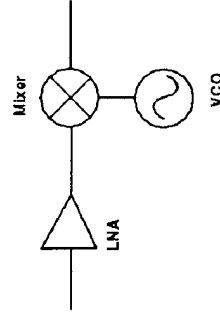


Power measurements at 1, 2, 5, & 10 GHz

## NEAR FUTURE

Fabrication in Progress:

- LNAs, Mixers, VCOs for operation @18-40 GHz
  - System-on-a-Chip @18 GHz
- Single-chip GPS receivers (~80-100 dB isolation)-SBIR '99
  - SiGe p-FET (> 100 GHz) & Logic



SIMULATED	Operating Freq	Gain	NF (50 $\Omega$ )	IP3 (output)	Power@vdd
LNA	18 GHz	15 db	3 dB	5dBm	22mW@1.5V
LNA/Differential	18 GHz	22 dB	3.7	10 dBm	60mW@1.5
Mixer	Center=16-20GHz IF=0.5-4 GHz	7 db	10 dB	5dBm	40mW@1.5V



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# Thin-film Silicon-on-Sapphire

## Characteristics

- Lower capacitance --> higher speed at lower power
- Fully depleted operation --> improved low voltage performance (esp. w.r.t. bipolar)
- Lower minority carrier lifetime
  - Parasitic bipolar suppressed
  - Higher S-D breakdown voltage
- Enhanced PMOS --> higher hole mobility than bulk Si, due to compressive stress (valence band splitting); better design flexibility for low power CMOS over GaAs (no p-channel)
- Excellent rf performance
  - $f_t > 100$  GHz for  $0.1 \mu\text{m}$   $L_{\text{eff}}$  n-type transistors
  - $f_{\text{max}} > 66/45$  GHz for  $.4 \mu\text{m}$  n/p-channel
  - Extremely low-loss substrate at rf (loss tangent  $< .0001$ )
- No parasitic coupling to substrate for passive components
- Good thermal conductivity
  - Higher than  $\text{SiO}_2$
  - Comparable to GaAs

# UHV/CVD Grown FET Structures

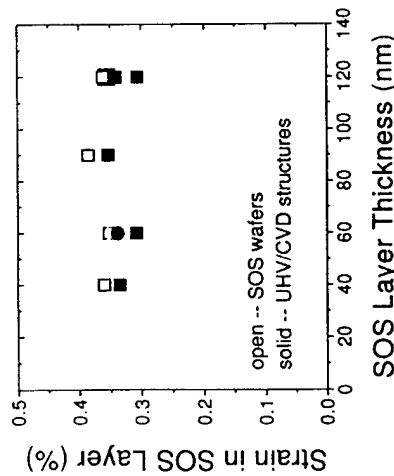
- SOS layer is compressively strained  $\sim 0.35\%$
- Remains  $\sim 0.30\%$  strained after UHV/CVD growth
- Low density of misfit dislocation at the Si/Al<sub>2</sub>O<sub>3</sub> interface

P. Mooney *et al.*, Appl. Phys. Lett. 73, pg. 924, 1998.

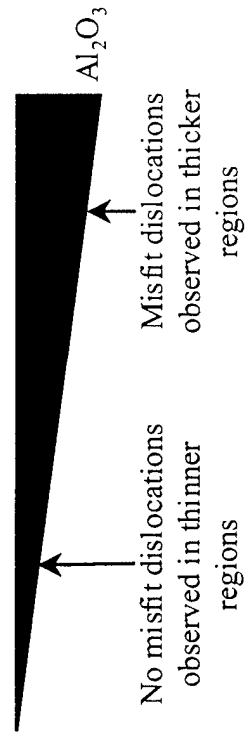
—Mat. Res. Soc. Symp. Proc., 533, pg. 55, 1998.

—To be published in *Applied Physics Letters*.

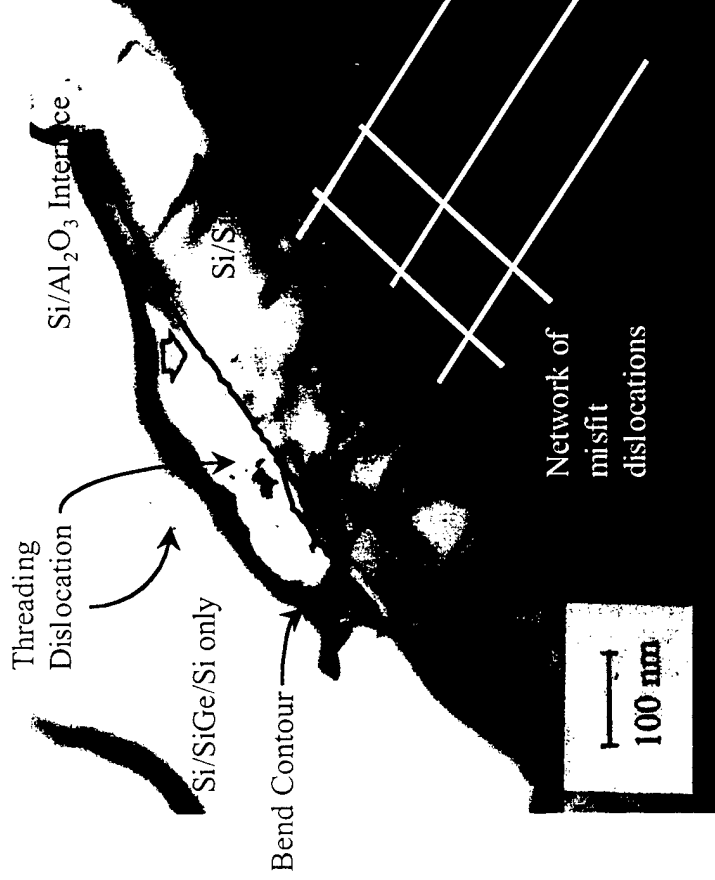
## X-ray diffraction



## Cross Section



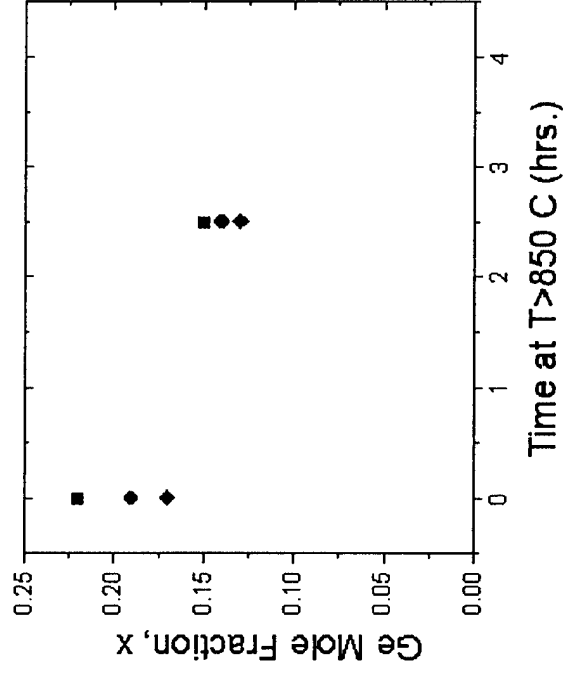
## Planar-view TEM



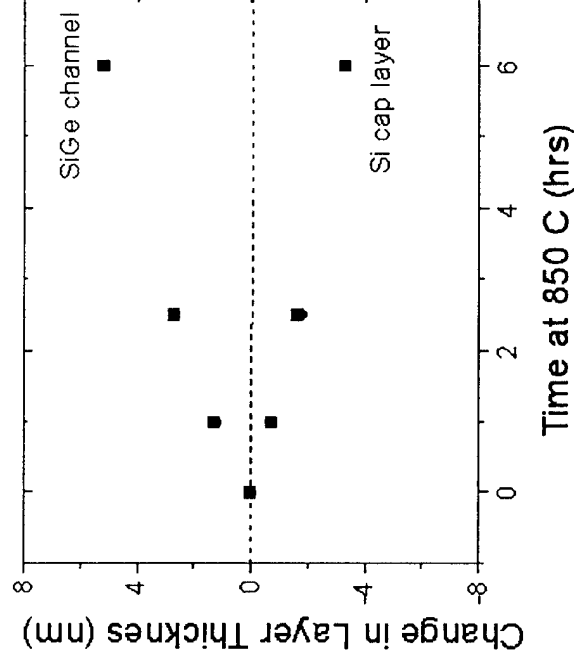
Arrows point to Si/Al<sub>2</sub>O<sub>3</sub> interface where misfit dislocations end

- Measured thickness and strain of Si layer, thickness and alloy composition of SiGe layer, and thickness of Si cap layer
- Showed that interdiffusion of Si and Ge at Si/SiGe interfaces occurs during thermal annealing at 850°C
- Demonstrated that SiGe layer structures were degraded by device fabrication processes at  $T > 800^{\circ}\text{C}$   
→ Low temperature processing required

Ge concentration in strained SiGe Layer over time at 850°C



SiGe strained layer thickness over time at 850°C



# SiGe FETs on Silicon-on-Sapphire Substrates

- **SiGe p-MOSFET Devices (Ge 20-30%)**
  - Hole mobilities 30 to 50% higher, up to 200  $\text{cm}^2/\text{V}\cdot\text{s}$  (S.J. Mathew *et al.*, Tech. Dig. 1997 Device Research Conf. and Electron Device Letters 20, 173 (1999))
- **New Approach: p-MODFET Devices**
  - Room temperature hole mobilities up to 1050  $\text{cm}^2/\text{Vs}$  in modulation doped structures on bulk Si (K. Ismail *et al.*, Appl./ Phys. Lett. 64, 3124 (1994))
  - $f_t = 70$  GHz for p-MODFETs on bulk Si (M. Arafa *et al.*, Electron Devices Lett. 17, 586 (1996))

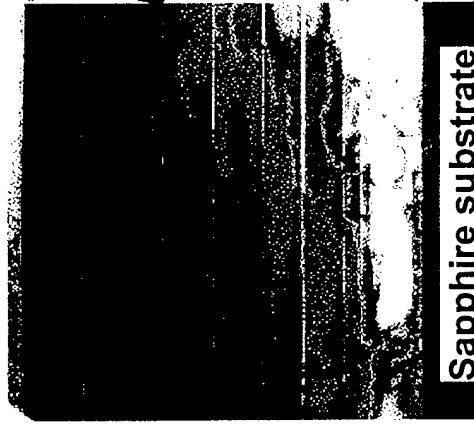
# Modulation-doped p-FET layers on SOS

Strained  $\text{Si}_{1-x}\text{Ge}_x$  device layer  
with unique profile,  $x > 0.75$

Uniform relaxed buffer  
layer  $\text{Si}_{0.65}\text{Ge}_{0.35}$

Step-Graded  
buffer layers

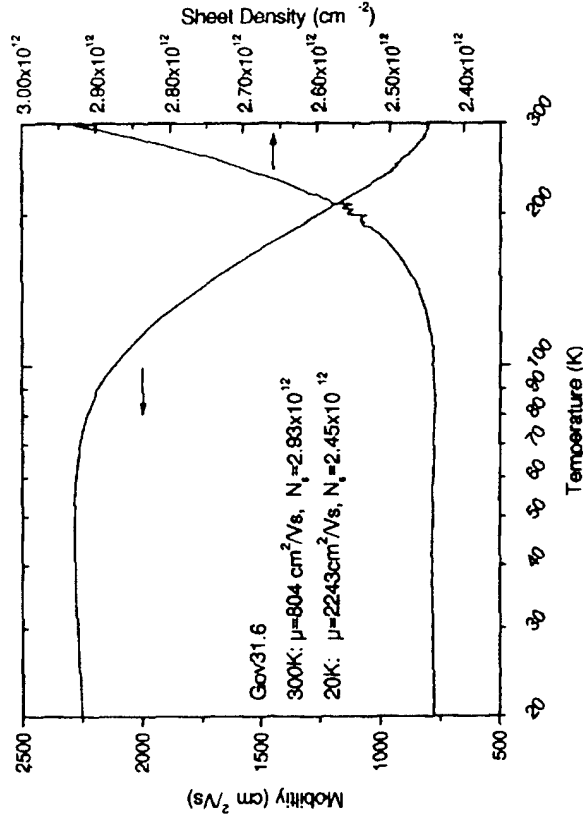
Starting  
silicon surface



Sapphire substrate

120 nm

Mobility and Sheet Hole  
Density vs. T



Hole mobility (300K):  $804 \text{ cm}^2/\text{V sec}$

Sheet hole density:  $2.5 \times 10^{12} \text{ cm}^{-2}$

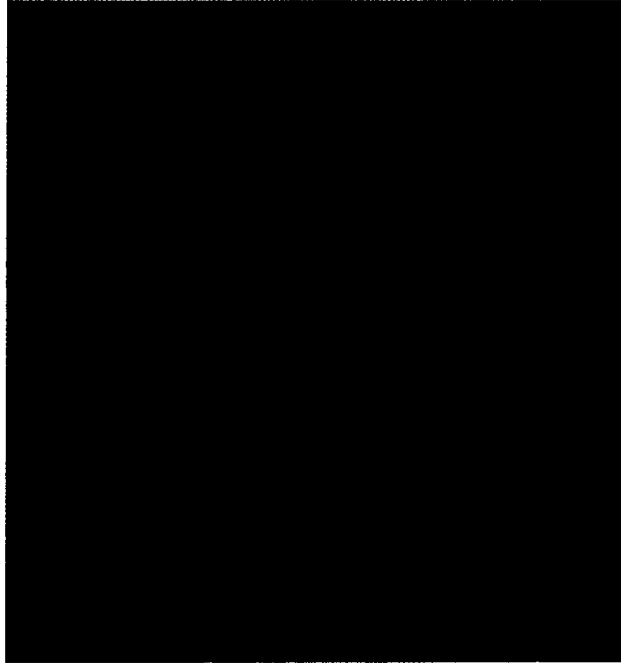
Active device layers are grown on top of a  
strain-relaxed SiGe buffer layer: total epi  
thickness approx. 1 micron



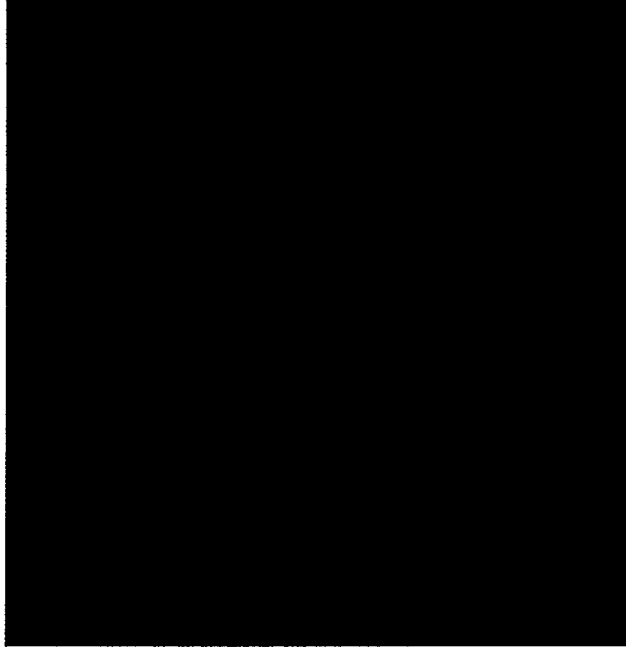
## Nomarski image of p-MODFET wafer surface

Gov32.6: 4" Union Carbide SOS substrate

Gov32.8: 4" bulk silicon



↕  
10  $\mu\text{m}$



- If not well-improved, large pits occur after SiGe growth at macro-twin defects in original SOS layer;
- Low defect density in SOS substrate required
- Wafer bonding methods have the potential to produce SOS substrates with
  - zero microtwin defects;
  - threading defect densities reduced by many orders of magnitude;
  - thin relaxed SiGe buffer layers on sapphire (required for fully depleted FETs)

## Closing Thoughts

- TFSOS addresses present and long-term issues and needs in battery-operated wireless communication and S to K-band (~40 GHz) applications providing unique solutions for low power System-on-a-Single-Chip, integrating analog and digital functions
- Focus of present and near-term
  - Strained SiGe (>75% Ge) on SOS to achieve high  $\mu_h$ 
    - $1/f_{p-SiGe/SOS} < 1/f_{p-SiGe/Si}$   
 $\Rightarrow$  Mixers with lower phase noise
    - $f_t, f_{max}$  highest ever, for low power CMOS and high performance ADCs
- SiGe p-FETs with greater or similar n-FET mobility will significantly reduce device size/chip area
  - higher CMOS performance products ( $f_t, f_{max} > 100\text{-}200\text{ GHz}$ ), for reduced system cost, using industrial IC infrastructure
- QHD simulation predicts similar device transconductance for SiGe on SOS FETs and AlGaAs/GaAs HEMTs (Prof. David Ferry, ASU, Seminar UCSD, May 26, 1998)
- World highest hole mobility ( $804\text{ cm}^2/\text{V}\cdot\text{sec}$  @300 K) measured on modulation-doped p-FET structure on TFSOS substrate
- MOSIS accepts TFSOS designs



## The Future

- Extend performance of silicon technology to K-band, benefiting from established industrial infrastructure resulting in lower cost
- TFSOS technology for digital and analog devices
  - 10 times lower power x delay product than conventional bulk technologies benefits in, e.g.,
    - Real-time sensor information processing
    - Radar image processing
    - Digital communication
  - Another factor of 5 reduction with low  $V_{dd}$ 
    - Deployable/Unattended situation awareness systems
    - Extended operation of all battery-powered systems
  - 10x greater immunity to SEU which benefits
    - All space based electronics
- TFSOS, a technology to implement advanced components, such as A/D converters, and single chip wireless communication systems



## The Future

- Extend performance of silicon technology with SiGe/TFSOS CMOS to K-band, benefiting from established industrial infrastructure resulting in lower cost, advanced components, such as A/DCs and wireless communication functions
- TFSOS, implementing a low power, lower cost, high performance technology for application to:
  - Space based electronics
  - Image processing
  - Digital communication
  - Extended operation battery-powered systems
  - Other commercial/military systems

*What all t he wise promised  
has not happened,  
and what all t he damned fools said  
would happen has come to pass*

**William Lamb  
Second Viscount Melbourne  
(from Lord Melbourne, 1834)**